

60V N-Channel Power MOSFET

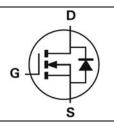
V_{DSS}, 60V

 $R_{DS(ON)}$, $9.3m\Omega$ (max.) @ $V_{GS}{=}10V$ $R_{DS(ON)}$, $11.2m\Omega$ (max.) @ $V_{GS}{=}4.5V$

 I_D , 17A







Description

The SG60N15S uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N15S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Para	ameter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current Continuous	T _A =25°C	L	17	Α
Drain Current-Continuous	T _A =70°C	ID I	14	Α
Drain Current-Pulsed Note 1		I _{DM}	67	А
Maximum Dayyar Dissination	T _A =25°C	D-	3.1	W
Maximum Power Dissipation	T _A =70°C	P _D	2.0	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	ge	TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	Steady State	-	-	75	°C/W
Maximum Junction-to-Ambient	Reja	t ≤ 10s	-	-	40	°C/W
Maximum Junction-to-Case	R _{0JC}	Steady State	-	-	24	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	60	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	

1



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ON CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.3	1.7	2.4	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =11A	-	-	9.3	mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =8A	-	-	11.2	mΩ	

DYNAMIC CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	Ciss		-	1486	-		
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, f=1MHz	-	123	-	pF	
Reverse Transfer Capacitance	Crss		-	71	-		

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	14.8	-	
Rise Time	tr	V_{GS} =10V, V_{DS} =30V, R_L =5 Ω ,	-	127	-]
Turn-Off Delay Time	T _{d(off)}	R _{GEN} =3Ω	- /-	54.2	-	ns
Fall Time	t _f			75.9	-	
Total Gate Charge	Qg		-	68	-	
Gate to Source Gate Charge	Qgs	V _{GS} =10V, V _{DS} =30V, I _D =10A		15.6	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	18	-	1
Gate resistance	Rg	V _{DS} =0V, V _{GS} =0V, f=1MHz	-	1.5	-	Ω

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1	V
Continuous Source Current	Is	V _G =V _D =0V , Force Current	-	-	17	Α
Pulsed Source Current	Ism	V _G -V _D -UV, Force Current	-	-	14	Α
Body Diode Reverse Recovery Time	trr	1 -404 -41/44-5004/	-	33	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	- I _F =10A, dl/dt=500A/µs	-	202	-	nC

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.



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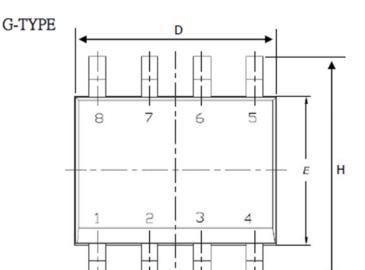
Marking Information

SOP-8 (S)	Marking Rule	
Laser Marking	Line 1 : Device Name	
	SG60N15S	
	<u>Line 2</u> : Date Code	
SG60N15S	YYMMXXX	
YYMMXXX	YY: Year Code	
	MM: Month Code	
	XXX : Serial Number	
Diagram		

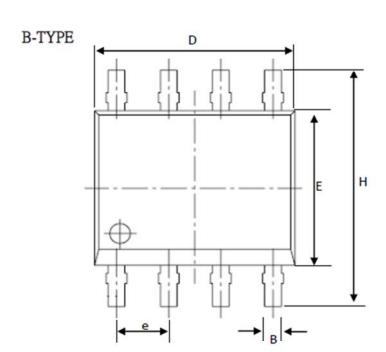


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Package of Dimension



Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
е	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00



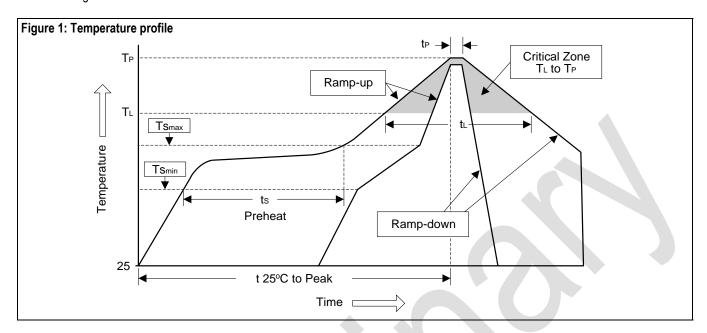




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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t⊳)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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6

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